Product Preview

Silicon Carbide Schottky Diode, 650 V, 40 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 94 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 Qualified
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

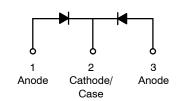
- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

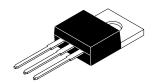


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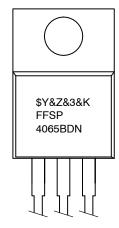


Schottky Diode



TO-220-3LD CASE 340AT

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code &K = Lot Code

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FFSP4065BDN

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

= Specific Device Code

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	Peak Repetitive Reverse Voltage Single Pulse Avalanche Energy (Note 1) Continuous Rectified Forward Current @ T _C < 136°C		V
E _{AS}	Single Pulse Avalanche Energy			mJ
I _F	Continuous Rectified Forward Current @ T _C <			Α
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	882	Α
		T _C = 150°C, 10 μs	798	Α
I _{F,SM}	Non-Repetitive Forward Surge Current $T_C = 25^{\circ}C$	Half-Sine Pulse, t _p = 8.3 ms	84	Α
Ptot	Power Dissipation	T _C = 25°C	95	W
		T _C = 150°C	16	W
T _J , T _{STG}	Operating and Storage Temperature Range TO247 Mounting Torque, M3 Screw		-55 to +175	°C
			60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	1.6*/0.8**	°C/W

^{*} Per Leg, ** Per Device

ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted (per leg))

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V_{F}	Forward Voltage	I _F = 20 A, T _C = 25°C	_	1.38	1.7	V
		I _F = 20 A, T _C = 125°C	_	1.6	2.0	
		I _F = 20 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	0.5	40	μΑ
		V _R = 650 V, T _C = 125°C	-	1	80	
		V _R = 650 V, T _C = 175°C	-	2	160	
Q _C	Total Capacitive Charge	V = 400 V	-	51	=	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	866	_	pF
		V _R = 300 V, f = 100 kHz	-	80	-	
		V _R = 600 V, f = 100 kHz	-	70	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSP4065BDN-F085	FFSP4065BDN	TO-220-3LD (Pb-Free / Halogen Free)	50 Units / Tube

^{*} Per Leg, ** Per Device

^{1.} E_{AS} of 94 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 19.4 A, V = 50 V.

TYPICAL CHARACTERISTICS

(T_J = 25°C unless otherwise noted (per leg))

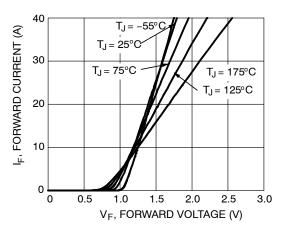


Figure 1. Forward Characteristics

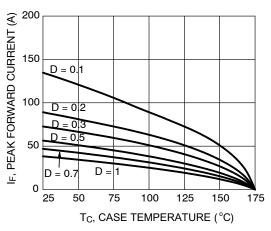


Figure 3. Current Derating

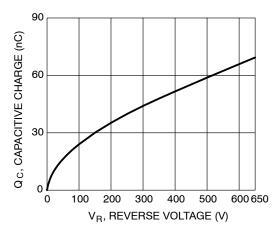


Figure 5. Capacitive Charge vs. Reverse Voltage

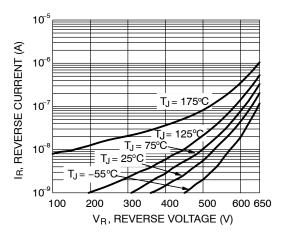


Figure 2. Reverse Characteristics

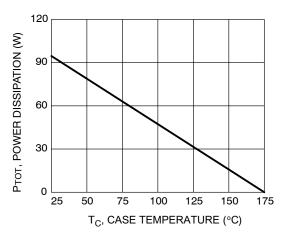


Figure 4. Power Derating

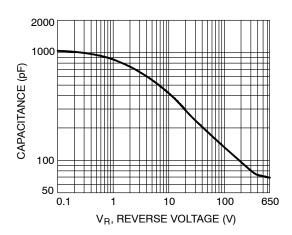


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

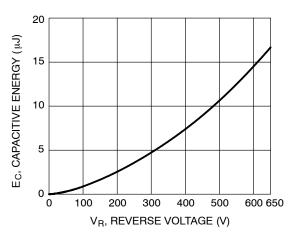


Figure 7. Capacitance Stored Energy

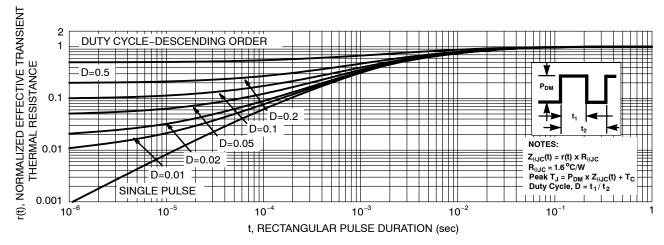


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

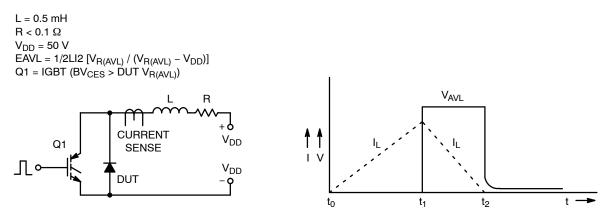
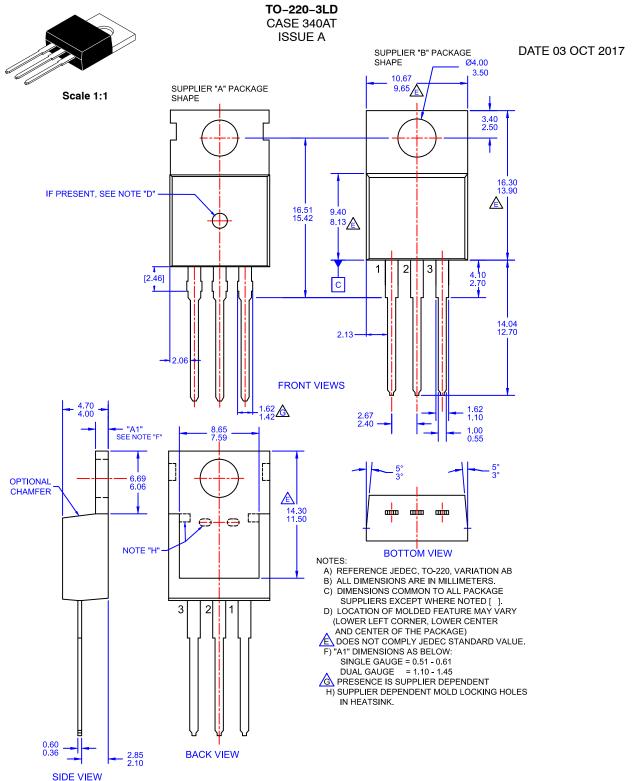


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



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